

## INCHANGE SEMICONDUCTOR

# isc N-Channel MOSFET Transistor

## FDD9411L

### FEATURES

- Drain Current : I\_D=25A@ T\_C=25 $^\circ\!\mathrm{C}$
- Drain Source Voltage
  : V<sub>DSS</sub>=40V(Min)
- Static Drain-Source On-Resistance
- : R<sub>DS(on)</sub> = 7m Ω (Max) @V<sub>GS</sub>= 10V
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRIPTION

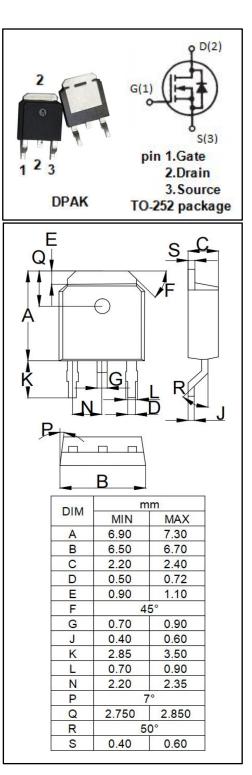
 motor drive, DC-DC converter, power switch and solenoid drive.

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL           | PARAMETER                              | VALUE   | UNIT |
|------------------|--|---------|------|
| V <sub>DSS</sub> | Drain-Source Voltage                   | 40      | V    |
| V <sub>GS</sub>  | Gate-Source Voltage-Continuous         | ±20     | V    |
| lD               | Drain Current-Continuous               | 25      | A    |
| IDM              | Drain Current-Single Pluse             | 100     | A    |
| P <sub>D</sub>   | Total Dissipation @T <sub>c</sub> =25℃ | 48.4    | W    |
| TJ               | Max. Operating Junction Temperature    | -55~175 | °C   |
| T <sub>stg</sub> | Storage Temperature                    | -55~175 | °C   |

#### THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                            | МАХ | UNIT |
|---------------------|--------------------------------------|-----|------|
| R <sub>th j-c</sub> | Thermal Resistance, Junction to Case | 3.1 | °C/W |





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### **ELECTRICAL CHARACTERISTICS**

#### T<sub>c</sub>=25℃ unless otherwise specified

| SYMBOL               | PARAMETER                       | CONDITIONS                                    | MIN | МАХ  | UNIT                 |
|----------------------|---------------------------------|---|-----|------|----------------------|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage  | V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA  | 40  | -    | V                    |
| V <sub>GS(th)</sub>  | Gate Threshold Voltage          | $V_{DS}$ = $V_{GS}$ ; I <sub>D</sub> = 0.25mA | 1.0 | 3.0  | V                    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance      | V <sub>GS</sub> = 10V; I <sub>D</sub> =20A    | -   | 7.0  | $\mathbf{m}  \Omega$ |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance      | V <sub>GS</sub> = 4.5V; I <sub>D</sub> =20A   | -   | 11.5 | $\mathbf{m}  \Omega$ |
| I <sub>GSS</sub>     | Gate-Body Leakage Current       | V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0    | -   | ±100 | nA                   |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current | V <sub>DS</sub> = 40V; V <sub>GS</sub> = 0    | -   | 1.0  | uA                   |
| V <sub>SD</sub>      | Forward On-Voltage              | I <sub>S</sub> =20A; V <sub>GS</sub> = 0      | _   | 1.25 | V                    |
| V <sub>SD</sub>      | Forward On-Voltage              | I <sub>S</sub> =10A; V <sub>GS</sub> = 0      | -   | 1.2  | V                    |

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